

Koichi Maezawa

List of Publications by Year in descending order

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1383
citing authors

#	ARTICLE	IF	CITATIONS
1	A study on current collapse in AlGaIn/GaN HEMTs induced by bias stress. IEEE Transactions on Electron Devices, 2003, 50, 2015-2020.	3.0	212
2	A New Resonant Tunneling Logic Gate Employing Monostable-Bistable Transition. Japanese Journal of Applied Physics, 1993, 32, L42-L44.	1.5	130
3	InP-based high-performance monostable-bistable transition logic elements (MOBILEs) using integrated multiple-input resonant-tunneling devices. IEEE Electron Device Letters, 1996, 17, 127-129.	3.9	124
4	Effects of surface passivation on breakdown of AlGaIn/GaN high-electron-mobility transistors. Applied Physics Letters, 2004, 84, 2184-2186.	3.3	124
5	High-performance InP-based enhancement-mode HEMTs using non-alloyed ohmic contacts and Pt-based buried-gate technologies. IEEE Transactions on Electron Devices, 1996, 43, 252-257.	3.0	123
6	High-speed and low-power operation of a resonant tunneling logic gate MOBILE. IEEE Electron Device Letters, 1998, 19, 80-82.	3.9	113
7	Functions and applications of monostable-bistable transition logic elements (MOBILE's) having multiple-input terminals. IEEE Transactions on Electron Devices, 1994, 41, 148-154.	3.0	107
8	Weighted sum threshold logic operation of MOBILE (monostable-bistable transition logic element) using resonant-tunneling transistors. IEEE Electron Device Letters, 1993, 14, 475-477.	3.9	69
9	Large Gate Leakage Current in AlGaIn/GaN High Electron Mobility Transistors. Japanese Journal of Applied Physics, 2002, 41, 5125-5126.	1.5	64
10	Drain Current DLTS of AlGaIn/GaN MIS-HEMTs. IEEE Electron Device Letters, 2004, 25, 523-525.	3.9	56
11	AlGaIn/GaN Heterostructure Metal-Insulator-Semiconductor High-Electron-Mobility Transistors with Si ₃ N ₄ Gate Insulator. Japanese Journal of Applied Physics, 2003, 42, 2278-2280.	1.5	51
12	Position-Controlled Carbon Nanotube Field-Effect Transistors Fabricated by Chemical Vapor Deposition Using Patterned Metal Catalyst. Japanese Journal of Applied Physics, 2003, 42, 4116-4119.	1.5	50
13	Drain current DLTS of AlGaIn/GaN HEMTs. Physica Status Solidi A, 2003, 200, 195-198.	1.7	48
14	Monolithic integration of resonant tunneling diodes and FET's for monostable-bistable transition logic elements (MOBILE's). IEEE Electron Device Letters, 1995, 16, 70-73.	3.9	44
15	Deep levels in n-type AlGaIn grown by hydride vapor-phase epitaxy on sapphire characterized by deep-level transient spectroscopy. Applied Physics Letters, 2005, 87, 2221-2223.	3.3	39
16	AlGaIn/GaN MIS-HEMTs with HfO ₂ gate insulator. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2700-2703.	0.8	38
17	Current Collapse in AlGaIn/GaN HEMTs Investigated by Electrical and Optical Characterizations. Physica Status Solidi A, 2002, 194, 447-451.	1.7	35
18	An exclusive-OR logic circuit based on controlled quenching of series-connected negative differential resistance devices. IEEE Electron Device Letters, 1996, 17, 309-311.	3.9	34

#	ARTICLE	IF	CITATIONS
19	Evaluation of effective electron velocity in AlGa _N /Ga _N HEMTs. Electronics Letters, 2000, 36, 1736.	1.0	31
20	Quasi-normally-off AlGa _N /Ga _N HEMTs fabricated by fluoride-based plasma treatment. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2732-2735.	0.8	31
21	Novel current-voltage characteristics in an In _{0.15} Ga _{0.85} As based resonant tunneling high electron mobility transistor. Applied Physics Letters, 1995, 67, 3608-3610.	3.3	27
22	88-GHz dynamic 2:1 frequency divider using resonant tunnelling chaos circuit. Electronics Letters, 2003, 39, 1546.	1.0	27
23	Effective mass and ground state of AlAs quantum wells studied by magnetoresistance measurements. Journal of Applied Physics, 1992, 71, 296-299.	2.5	24
24	Magnetic phase diagram and the pressure and field dependence of the Fermi surface in UGe ₂ . Physical Review B, 2002, 65, .	3.2	24
25	ESR Study of Low Temperature Phase Transitions in Se Doped LiKSO ₄ . Journal of the Physical Society of Japan, 1985, 54, 3106-3110.	1.6	23
26	Temperature dependence of high-frequency performance of AlGaAs/InGaAs pseudomorphic HEMT's. IEEE Electron Device Letters, 1992, 13, 8-10.	3.9	23
27	High-speed operation of static binary frequency divider using resonant tunnelling diodes and HEMTs. Electronics Letters, 1998, 34, 70.	1.0	22
28	Spin fluctuations and non-Fermi-liquid behavior of CeNi ₂ Ge ₂ . Physical Review B, 2003, 68, .	3.2	22
29	Surface Potential Measurement of Carbon Nanotube Field-Effect Transistors Using Kelvin Probe Force Microscopy. Japanese Journal of Applied Physics, 2007, 46, 2496-2500.	1.5	22
30	Temperature Distribution Measurement in AlGa _N /Ga _N High-Electron-Mobility Transistors by Micro-Raman Scattering Spectroscopy. Japanese Journal of Applied Physics, 2002, 41, L452-L454.	1.5	21
31	Fluidic Assembly of Thin GaAs Blocks on Si Substrates. Japanese Journal of Applied Physics, 2003, 42, 2226-2229.	1.5	21
32	Large transconductance n ⁺ -Ge gate AlGaAs/GaAs MISFET with thin gate insulator. IEEE Electron Device Letters, 1986, 7, 454-456.	3.9	20
33	Resonant Tunneling in a Novel Coupled-Quantum-Well Base Transistor. Japanese Journal of Applied Physics, 1991, 30, L2018-L2020.	1.5	20
34	Monostable-Bistable Transition Logic Elements (MOBILEs) Based on Monolithic Integration of Resonant Tunneling Diodes and FETs. Japanese Journal of Applied Physics, 1995, 34, 1199-1203.	1.5	20
35	Measurement of Contact Potential of GaAs pn Junctions by Kelvin Probe Force Microscopy. Japanese Journal of Applied Physics, 1999, 38, 4893-4894.	1.5	19
36	Superconductivity, upper critical field and normal state resistivity in CeNi ₂ Ge ₂ under pressure. Journal of Physics Condensed Matter, 2000, 12, 1339-1349.	1.8	19

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37	Surface potential measurements of AlGaIn-GaN high-electron-mobility transistors by Kelvin probe force microscopy. Applied Physics Letters, 2004, 85, 6028-6029.	3.3	19
38	Barrier Height in Indirect Bandgap AlGaAs/GaAs Hetero-Junction Determined with n-Semiconductor/Insulator/Semiconductor Diodes. Japanese Journal of Applied Physics, 1986, 25, L557-L559.	1.5	18
39	Compensation Mechanism in Heavily Si-Doped GaAs Grown by MBE. Japanese Journal of Applied Physics, 1990, 29, L527-L529.	1.5	18
40	Monte Carlo Study of Charge Injection Transistors (CHINTs). Japanese Journal of Applied Physics, 1993, 32, 26-30.	1.5	18
41	InP-Based High-Performance Monostable-Bistable Transition Logic Element (MOBILE): an Intelligent Logic Gate Featuring Weighted-Sum Threshold Operations. Japanese Journal of Applied Physics, 1996, 35, 1172-1177.	1.5	18
42	Study on off-state breakdown in AlGaIn/GaN HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2335-2338.	0.8	18
43	High-Frequency Characteristics of Charge-Injection Transistor-Mode Operation in AlGaAs/InGaAs/GaAs Metal-Insulator-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 1991, 30, 1190-1193.	1.5	17
44	Analysis of Switching Time of Monostable-Bistable Transition Logic Elements Based on Simple Model Calculation. Japanese Journal of Applied Physics, 1995, 34, 1213-1217.	1.5	17
45	High-speed operation of resonant tunnelling flip-flop circuit employing MOBILE (monostable-bistable) Tj ETQq1 1 0,784314 r _{BT} /Ove	1.0	17
46	Static frequency divider featuring reduced circuit complexity by utilizing resonant tunneling diodes in combination with HEMTs. IEEE Electron Device Letters, 1997, 18, 544-546.	3.9	16
47	Resonant Tunneling Chaos Generator for High-Speed/Low-Power Frequency Divider. Japanese Journal of Applied Physics, 1999, 38, L1321-L1322.	1.5	16
48	X-conduction-electron transport in very thin AlAs quantum wells. Physical Review B, 1994, 49, 2189-2192.	3.2	15
49	Improved source resistance in InP-based enhancement-mode HEMTs for high speed digital applications. Electronics Letters, 1995, 31, 925-927.	1.0	15
50	High Quality InSb Films Grown on Si(111) Substrate via InSb Bi-Layer. E-Journal of Surface Science and Nanotechnology, 2009, 7, 145-148.	0.4	15
51	High-temperature growth of heteroepitaxial InSb films on Si(1 1 1) substrate via the InSb bi-layer. Journal of Crystal Growth, 2009, 311, 1692-1695.	1.5	15
52	Potential profile measurement of GaAs MESFETs passivated with low-temperature grown GaAs layer by Kelvin probe force microscopy. Solid-State Electronics, 1999, 43, 1547-1553.	1.4	14
53	Robust Operation of a Novel Frequency Divider Using Resonant Tunneling Chaos Circuit. Japanese Journal of Applied Physics, 2000, 39, 3334-3338.	1.5	14
54	Direct integration of GaAs HEMTs on AlN ceramic substrates using fluidic self-assembly. Electronics Letters, 2005, 41, 1275.	1.0	14

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55	High-pressure resistivity and lattice parameters of CeNi ₂ Ge ₂ . Physica B: Condensed Matter, 1997, 230-232, 198-200.	2.7	13
56	Electroluminescence in AlGa _N /Ga _N High Electron Mobility Transistors under High Bias Voltage. Japanese Journal of Applied Physics, 2002, 41, 1990-1991.	1.5	13
57	50 GHz frequency divider using resonant tunnelling chaos circuit. Electronics Letters, 2002, 38, 305.	1.0	13
58	Resonant tunnelling delta sigma modulator suitable for high-speed operation. Electronics Letters, 2006, 42, 77.	1.0	12
59	100 GHz Operation of a Resonant Tunneling Logic Gate MOBILE Having a Symmetric Configuration. , 0, , .		12
60	A Novel Delayed Flip-Flop Circuit Using Resonant Tunneling Logic Gates. Japanese Journal of Applied Physics, 1998, 37, L212-L213.	1.5	11
61	Uniformity of the High Electron Mobility Transistors and Resonant Tunneling Diodes Integrated on an InP Substrate Using an Epitaxial Structure Grown by Molecular Beam Epitaxy and Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1998, 37, 5500-5502.	1.5	11
62	Measurement of Contact Potential of GaAs/AlGaAs Heterostructure Using Kelvin Probe Force Microscopy. Japanese Journal of Applied Physics, 1999, 38, L767-L769.	1.5	11
63	A Delta-Sigma Analog-to-Digital Converter Using Resonant Tunneling Diodes. Japanese Journal of Applied Physics, 2001, 40, L1005-L1007.	1.5	11
64	High-Speed Operation of a Novel Frequency Divider Using Resonant Tunneling Chaos Circuit. Japanese Journal of Applied Physics, 2002, 41, 1150-1153.	1.5	11
65	Measurement of Frequency Dispersion of AlGa _N /Ga _N High Electron Mobility Transistors. Japanese Journal of Applied Physics, 2003, 42, 424-425.	1.5	11
66	Submicrometer n ⁺ /sup +/-Ge gate AlGaAs/GaAs MISFETs. IEEE Transactions on Electron Devices, 1989, 36, 2217-2222.	3.0	10
67	Magnetic properties and Fermi surface of antiferromagnetic SmCu ₆ . Physical Review B, 1990, 41, 568-572.	3.2	10
68	Effects of Deposition Conditions of First InSb Layer on Electrical Properties of n-Type InSb Films Grown With Two-Step Growth Method via InSb Bilayer. Japanese Journal of Applied Physics, 2011, 50, 04DH13.	1.5	10
69	Experimental demonstration of strain detection using resonant tunneling delta sigma modulation sensors. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600548.	1.8	10
70	Characterization of Lattice Sites and Compensation Mechanism in Heavily Si-Doped GaAs with Laser Raman Spectroscopy. Japanese Journal of Applied Physics, 1990, 29, 301-304.	1.5	9
71	X conduction two-dimensional subband structure and order in AlGaAs/AlAs quantum wells. Physica B: Condensed Matter, 1994, 201, 295-300.	2.7	9
72	Reset-set flipflop based on a novel approach of modulating resonant-tunnelling current with FET gates. Electronics Letters, 1994, 30, 1805-1806.	1.0	9

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73	Resonant tunneling diodes and their application to high-speed circuits. , 2005, , .		9
74	Heteroepitaxial InSb films grown via Si(111)- $\sqrt{3}\times\sqrt{3}$ -In surface reconstruction. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2772-2774.	0.8	9
75	Growing and purification of a CeCu ₆ single crystal. Journal of Magnetism and Magnetic Materials, 1987, 63-64, 306-308.	2.3	8
76	High-speed operation of a resonant tunneling flip-flop circuit employing a MOBILE (monostable-bistable transition logic element). , 0, , .		8
77	Highly Uniform Regrown In _{0.53} Ga _{0.47} As/AlAs/InAs Resonant Tunneling Diodes on In _{0.53} Ga _{0.47} As. Japanese Journal of Applied Physics, 1999, 38, 1204-1207.	1.5	8
78	Direct Observation of High-Frequency Chaos Signals from the Resonant Tunneling Chaos Generator. Japanese Journal of Applied Physics, 2004, 43, 5235-5238.	1.5	8
79	Effects of In and Sb mono-layers to form rotated InSb films on a Si(111) substrate. Applied Surface Science, 2008, 254, 6052-6054.	6.1	8
80	Ultrashort Pulse Generators Using Resonant Tunneling Diodes and Their Integration with Antennas on Ceramic Substrates. Japanese Journal of Applied Physics, 2008, 47, 2833-2837.	1.5	8
81	Improved Bias Stability of the Resonant Tunneling Diode Pair Oscillators Integrated on an AlN Ceramic Substrate. Japanese Journal of Applied Physics, 2009, 48, 04C084.	1.5	8
82	InSb films grown on the V-grooved Si(001) substrate with InSb bilayer. Physics Procedia, 2010, 3, 1335-1339.	1.2	8
83	Possibilities of Large Voltage Swing Hard-Type Oscillators Based on Series-Connected Resonant Tunneling Diodes. IEICE Transactions on Electronics, 2018, E101.C, 305-310.	0.6	8
84	Optically excited minority-carrier electron velocity in selectively Be-doped AlGaAs/GaAs/AlGaAs single quantum wells. Applied Physics Letters, 1990, 56, 1146-1148.	3.3	7
85	Novel current-voltage characteristics of an InP-based resonant-tunneling high electron mobility transistor and their circuit applications. , 0, , .		7
86	Possibility of Terahertz Amplification by Active Transmission Lines Loaded with Resonant Tunneling Diode Pairs. Japanese Journal of Applied Physics, 2009, 48, 124503.	1.5	7
87	Characterization of Al ₂ O ₃ /InSb/Si MOS diodes having various InSb thicknesses grown on Si(1 1 1) substrates. Semiconductor Science and Technology, 2012, 27, 045007.	2.0	7
88	Effective Mobility Enhancement in Al ₂ O ₃ /InSb/Si Quantum Well Metal Oxide Semiconductor Field Effect Transistors for Thin InSb Channel Layers. Japanese Journal of Applied Physics, 2013, 52, 04CF01.	1.5	7
89	Delta- σ modulation microphone sensors using microwave cavity resonator. Electronics Letters, 2016, 52, 1651-1652.	1.0	7
90	An AlGaAs/In _x Ga _{1-x} As/AlGaAs (0x=0.5) pseudomorphic HEMT on GaAs substrate using an In _{x/2} Ga _{1-x/2} As buffer layer. IEEE Transactions on Electron Devices, 1990, 37, 1416-1421.	3.0	6

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91	Dual-Wavelength High-Power Laser Diodes Fabricated by Selective Fluidic Self-Assembly. Japanese Journal of Applied Physics, 2005, 44, 2568-2571.	1.5	6
92	High-Power Oscillations in Resonant Tunneling Diode Pair Oscillator ICs Fabricated with Metamorphic devices. Japanese Journal of Applied Physics, 2007, 46, 2306-2308.	1.5	6
93	Step Hall Measurement of InSb Films Grown on Si(111) Substrate Using InSb Bilayer. Japanese Journal of Applied Physics, 2011, 50, 01BF01.	1.5	6
94	Characterization of a hard-type oscillator using series-connected tunnel diodes. IEICE Electronics Express, 2018, 15, 20180355-20180355.	0.8	6
95	Study on impedance matching and maximum wireless power transfer efficiency of circuits with resonant coupling based on simplified S -matrix. IEICE Electronics Express, 2019, 16, 20190156-20190156.	0.8	6
96	Electrical characteristics of Be-implanted GaAs activated by rapid thermal annealing. IEEE Electron Device Letters, 1986, 7, 13-15.	3.9	5
97	Clear negative characteristics observed in coupled-quantum-well base resonant tunneling transistors. IEEE Electron Device Letters, 1993, 14, 202-204.	3.9	5
98	Threshold Logic Function on Both Positive and Negative Weighted Sums in Multiple-Input Monostable-Bistable Transition Logic Elements. Japanese Journal of Applied Physics, 1994, 33, 794-797.	1.5	5
99	Large-signal microwave characteristics of resonant-tunneling high electron mobility transistors. IEEE Transactions on Electron Devices, 1999, 46, 281-287.	3.0	5
100	Fluid Dynamic Assembly of Semiconductor Blocks for Heterogeneous Integration. Japanese Journal of Applied Physics, 2004, 43, 5951-5954.	1.5	5
101	Metamorphic Resonant Tunneling Diodes and Its Application to Chaos Generator ICs. Japanese Journal of Applied Physics, 2005, 44, 4790-4794.	1.5	5
102	Effects of Initial In Coverage for Preparation of InSb Bilayer on Electrical Properties of InSb Films Grown By Surface Reconstruction Controlled Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH03.	1.5	5
103	Heteroepitaxial growth of InGaSb on GaSb/Si(111) As-AsGa surface phase with a two-step growth method to investigate the impact of high-quality GaSb buffer layer. Physica Status Solidi (B): Basic Research, 2017, 254, 1600528.	1.5	5
104	Low-Loss Characteristics of Metal-Foil-Based Passive Components by Surface-Activated Bonding Technologies. IEEE Transactions on Electron Devices, 2019, 66, 3946-3952.	3.0	5
105	Effects of Deposition Conditions of First InSb Layer on Electrical Properties of n-Type InSb Films Grown With Two-Step Growth Method via InSb Bilayer. Japanese Journal of Applied Physics, 2011, 50, 04DH13.	1.5	5
106	Monte Carlo Simulation of Response Time for Velocity Modulation Transistors. Japanese Journal of Applied Physics, 1992, 31, 757-760.	1.5	4
107	More flexible and simpler logic circuits implemented with resonant tunneling transistors. IEEE Transactions on Electron Devices, 1995, 42, 1005-1007.	3.0	4
108	A Large Output Voltage Swing of a Resonant Tunneling Flip-Flop Circuit Employing a Monostable-Bistable Transition Logic Element (MOBILE). Japanese Journal of Applied Physics, 1998, 37, L1286-L1287.	1.5	4

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109	Measurements of Electroluminescence Intensity Distribution in the Direction of Gate Width of n+Self-Aligned Gate GaAs Metal-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 1999, 38, 1363-1364.	1.5	4
110	Observation of resonant tunneling through single self-assembled InAs quantum dots using electrophotoluminescence spectroscopy. Journal of Applied Physics, 2000, 87, 4332-4336.	2.5	4
111	Temperature Distributions in AlGaIn/GaN HEMTs Measured by Micro-Raman Scattering Spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 57-60.	0.8	4
112	A new generation of negative-resistance devices—New developments in ultrahigh-frequency applications based on resonant tunneling elements. Electronics and Communications in Japan, 2006, 89, 29-38.	0.2	4
113	Experimental Demonstration of Ideal Noise Shaping in Resonant Tunneling Delta-Sigma Modulator for High Resolution, Wide Band Analog-to-Digital Converters. Japanese Journal of Applied Physics, 2006, 45, 3410-3413.	1.5	4
114	Full-wave analysis of traveling pulses developed in a system of transmission lines with regularly spaced resonant tunneling diodes. International Journal of Circuit Theory and Applications, 2018, 46, 671-682.	2.0	4
115	Delta-sigma modulation microphone sensors employing a resonant tunneling diode with a suspended microstrip resonator. Sensor Review, 2020, 40, 535-542.	1.8	4
116	Effects of Oscillator Phase Noise on Frequency Delta Sigma Modulators with a High Oversampling Ratio for Sensor Applications. IEICE Transactions on Electronics, 2021, E104.C, 463-466.	0.6	4
117	A Proposal of High-Performance Samplers Based on Resonant Tunneling Diodes. IEICE Transactions on Electronics, 2012, E95.C, 1830-1833.	0.6	4
118	Effects of Initial In Coverage for Preparation of InSb Bilayer on Electrical Properties of InSb Films Grown By Surface Reconstruction Controlled Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH03.	1.5	4
119	An AlGaAs/InGaAs/GaAs Strained Channel MISFET. Japanese Journal of Applied Physics, 1987, 26, L74-L76.	1.5	3
120	A high-speed frequency divider using n+-Ge Gate AlGaAs/GaAs MISFET's. IEEE Electron Device Letters, 1987, 8, 226-227.	3.9	3
121	High-frequency small-signal and large-signal characteristics of resonant tunneling high electron mobility transistors (RHEMTs). IEEE Transactions on Electron Devices, 1997, 44, 2038-2040.	3.0	3
122	Photoluminescence Study of Resonant Tunneling Transistor with p+/n-Junction Gate. Japanese Journal of Applied Physics, 2000, 39, 35-40.	1.5	3
123	Effects of the HEMT parameters on the operation frequency of resonant tunneling logic gate MOBILE. Electronics and Communications in Japan, 2002, 85, 1-6.	0.2	3
124	Comparison of Electrical Characteristics of Metamorphic HEMTs with InP HEMTs and PHEMTs. Japanese Journal of Applied Physics, 2003, 42, 2219-2222.	1.5	3
125	Characterization of Electrical Properties of Micro-Schottky Contacts on Epitaxial Lateral Overgrowth GaN. Japanese Journal of Applied Physics, 2003, 42, 2250-2253.	1.5	3
126	Controlling high-frequency chaos in resonant tunneling chaos generator circuits. IEICE Electronics Express, 2005, 2, 368-372.	0.8	3

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127	Dual-clock MASH delta-sigma modulator employing a frequency modulated intermediate signal. IEICE Electronics Express, 2006, 3, 459-463.	0.8	3
128	Heteroepitaxial growth of InSb films on the patterned Si(001) substrate. Physics Procedia, 2010, 3, 1329-1333.	1.2	3
129	Growth Nature of InSb Channel Layer on Heteroepitaxial Films of InGaSb Layer on GaSb/Si(111)- $\sqrt{3}\sqrt{3}$ -Ga Surface Phase. E-Journal of Surface Science and Nanotechnology, 2018, 16, 20-26.	0.4	3
130	An investigation of the crystalline nature for GaSb films on Si(111) at varied growth temperature and growth rate. Japanese Journal of Applied Physics, 2019, 58, S11A17.	1.5	3
131	Experimental observation of synchronised oscillating edges in electrical lattice with series-connected tunnel diodes. Electronics Letters, 2019, 55, 14-16.	1.0	3
132	Large-amplitude voltage edge oscillating in a transmission line with regularly spaced series-connected resonant-tunneling diodes. IEICE Electronics Express, 2018, 15, 20180678-20180678.	0.8	3
133	Identification of Vacancy-Type Defects in Molecular Beam Epitaxy-Grown GaAs Using a Slow Positron Beam. Japanese Journal of Applied Physics, 1992, 31, 2056-2060.	1.5	2
134	Analysis of microwave characteristics of a double-channel FET employing the velocity-modulation transistor concept. IEEE Transactions on Electron Devices, 1992, 39, 2438-2443.	3.0	2
135	A novel ultrafast functional device: resonant tunneling high electron mobility transistor. , 0, , .		2
136	Resistive-fuse network for early vision using resonant tunnelling diodes and HEMTs on an InP substrate. Electronics Letters, 1997, 33, 722.	1.0	2
137	Sampling phase detector using a resonant tunneling high electron mobility transistor for microwave phase-locked oscillators. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 1998, 6, 39-42.	3.1	2
138	AlGaIn/GaN High Electron Mobility Transistors with Inclined-Gate-Recess Structure. Japanese Journal of Applied Physics, 2006, 45, 3368-3371.	1.5	2
139	InP-based Resonant Tunneling Diode/HEMT Integrated Circuits for Ultrahigh-Speed Operation. , 0, , .		2
140	A GaAs SOI HEMT Fabricated by Fluidic Self-Assembly and Its Application to an RF-Switch. IEICE Transactions on Electronics, 2008, E91-C, 1025-1030.	0.6	2
141	Heteroepitaxial growth of a rotated AlInSb layer mediated by an InSb bi-layer on a Si(111) substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1497-1500.	0.8	2
142	A traveling wave amplifier based on composite right/left handed (CRLH) transmission lines periodically loaded with resonant tunneling diode pairs. , 2010, , .		2
143	Noise Floor Reduction in Frequency Delta-Sigma Modulation Microphone Sensors. Sensors, 2021, 21, 3470.	3.8	2
144	Heteroepitaxial Growth of InSb Films on V-Grooved Si(001) Substrate. E-Journal of Surface Science and Nanotechnology, 2009, 7, 669-672.	0.4	2

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145	Al-foil-based low-loss coplanar waveguides directly bonded to sapphire substrates. , 2017, , .		2
146	A highly mismatched $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{AlGaAs}$ ($0 \leq x \leq 0.5$) pseudomorphic HEMT on GaAs substrate using an $\text{In}_x/2\text{Ga}_{1-x}/2\text{As}$ buffer layer. <i>Solid-State Electronics</i> , 1997, 41, 1469-1474.	1.4	1
147	Observation of high field regions in GaAs MESFETs by using Kelvin probe force microscopy. , 0, , .		1
148	Position-controlled carbon nanotube FETs fabricated by CVD synthesis using patterned metal catalyst. , 0, , .		1
149	Experimental Demonstration of Capacitor-Coupled Resonant Tunneling Logic Gates for Ultra-short Gate-delay Operation. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 6766-6771.	1.5	1
150	Applications of high-frequency chaos in resonant tunneling chaos generator circuits. , 0, , .		1
151	Magnetic field effect on the T2 coefficient of the resistivity in the ferromagnetic superconductor UGe_2 . <i>Physica B: Condensed Matter</i> , 2005, 359-361, 1060-1062.	2.7	1
152	A Third Order Harmonic Oscillator Based on Coupled Resonant Tunneling Diode Pair Oscillators. <i>IEICE Transactions on Electronics</i> , 2010, E93-C, 1290-1294.	0.6	1
153	$\text{AlInGaAs}/\text{InSb}/\text{Si}$ quantum well MOSFETs having an ultra-thin InSb layer. , 2012, , .		1
154	Fluidic Self-Assembly Using Molten Ga Bumps and Its Application to Resonant Tunneling Diodes. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 116501.	1.5	1
155	Possibility of THz detection with resonant tunneling super regenerative detectors based on extremely high order harmonics. <i>IEICE Electronics Express</i> , 2013, 10, 20130676-20130676.	0.8	1
156	Current Collapse in $\text{AlGaIn}/\text{GaIn}$ HEMTs Investigated by Electrical and Optical Characterizations. , 2002, 194, 447.		1
157	Possibility of High Order Harmonic Oscillators Based on Active Transmission Lines Loaded with Resonant Tunneling Diode Pairs. <i>IEICE Transactions on Electronics</i> , 2012, E95.C, 1385-1388.	0.6	1
158	Fabrication and Characterization of Micromachined Cantilever Loaded with a Resonant Tunneling Diode for Delta-Sigma Type Strain Sensor Applications. , 2013, , .		1
159	Step Hall Measurement of InSb Films Grown on Si(111) Substrate Using InSb Bilayer. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 01BF01.	1.5	1
160	Low-loss characteristics of coplanar waveguides fabricated by directly bonding metal foils to high-resistivity Si substrates. <i>Japanese Journal of Applied Physics</i> , 0, , .	1.5	1
161	Improvement of Ge/AlGaAs Air-Exposed Interfaces Grown by MBE and Their Application to n^+ -Ge Gate $\text{AlGaAs}/\text{GaAs}$ MISFETs. <i>Japanese Journal of Applied Physics</i> , 1989, 28, 748-753.	1.5	0
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